

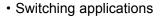
Isc N-Channel MOSFET Transistor

SPA11N65C3

• FEATURES

- With TO-220F Package
- Drain Source Voltage-
 - : V_{DSS}=650V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.38 \Omega (Max)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



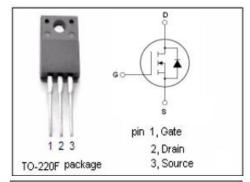


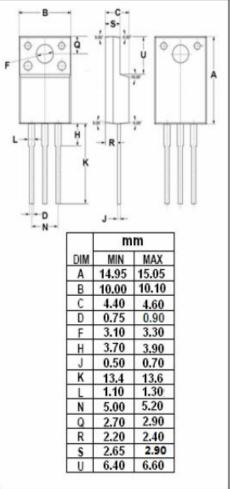
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	650	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous @Tc=25°C (V _{GS} at 10V) Tc=100°C	11 7	А
I _{DM}	Drain Current-Single Pulsed	33	Α
P _D	Total Dissipation @T _c =25℃	33	W
Tj	Max. Operating Junction Temperature	-55~150	$^{\circ}$ C
T _{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.8	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	80	°C/W





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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	650			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =500uA	2.1	3	3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =7A		0.34	0.38	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V;Tj=25°C V _{DS} = 600V; V _{GS} = 0V; Tj=150°C		0.1	1 100	μА
V _{SDF}	Diode forward voltage	I _{SD} = 11A, V _{GS} = 0 V		1	1.2	V



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